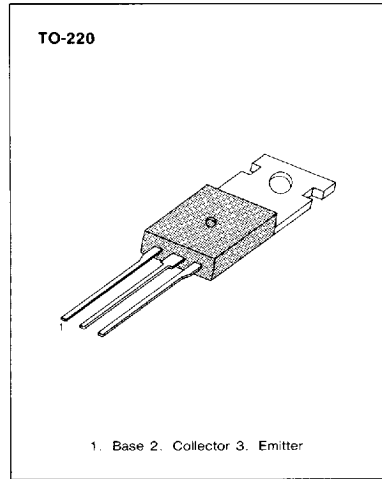


HIGH VOLTAGE POWER SWITCH
SWITCHING APPLICATION

ABSOLUTE MIXIMUM RATING($T_a=25^{\circ}C$)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	800	V
Collector Emitter Voltage	V_{CEO}	400	V
Emitter Base Voltage	V_{EBO}	7	V
Collector Current(DC)	I_C	5	A
Collector Current(Pulse)	I_C	10	A
Base Current	I_B	3	A
Collector Dissipation	P_C	70	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-65~150	$^{\circ}C$



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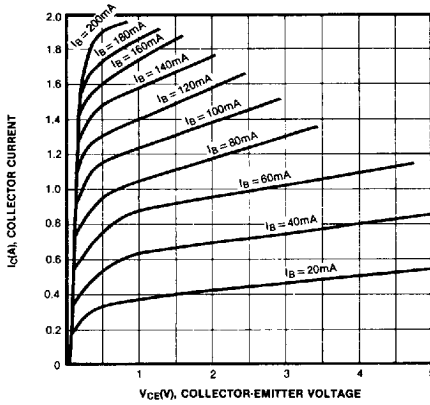
ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=1mA, I_E=0$	800			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=5mA, I_B=0$	400			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_C=1mA, I_C=0$	7			V
Collector Cutoff Current	I_{CBO}	$V_{CB}=500V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=7V, I_C=0$			10	μA
*DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=0.3A$	10			
*Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.5A, I_B=0.5A$			1.5	V
*Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2.5A, I_B=0.5A$			2.0	V
Current Gain Bandwidth Product	f_T	$V_{CE}=5V, I_C=0.1A$		10		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		40		pF
Turn On Time	t_{on}	$I_{B1} = I_{B2}=0.5A$			1	μS
Storage Time	t_{stg}	$I_C=2.5A$			3	μS
Fall Time	t_f	$V_{CC}=150V$			0.8	μS

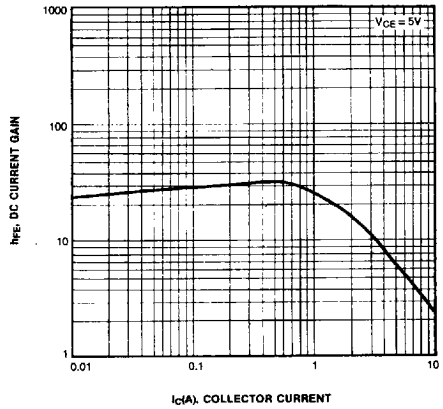
* Plus test: PW=300 μs , Duty Cycle=2% Pulsed



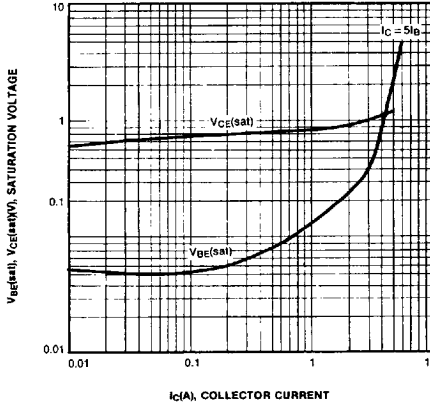
STATIC CHARACTERISTIC



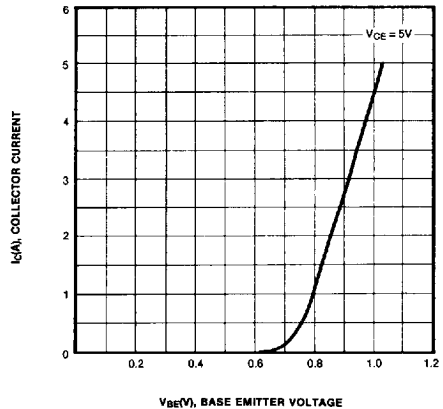
DC CURRENT GAIN



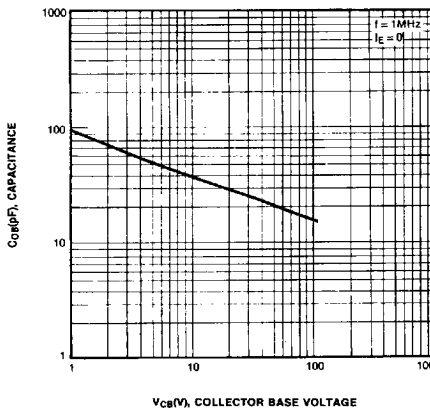
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



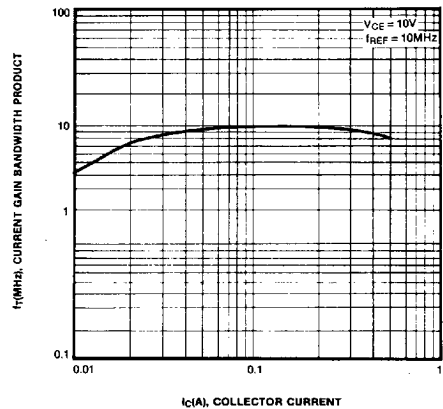
BASE-EMITTER ON VOLTAGE



COLLECTOR OUTPUT CAPACITANCE

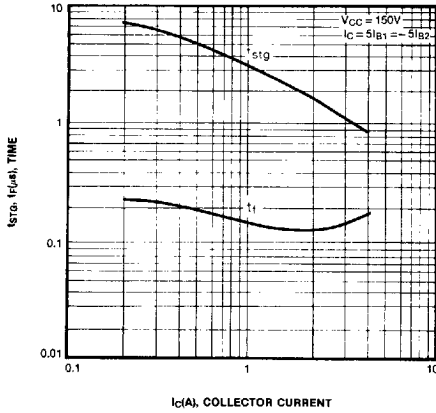


CURRENT GAIN BANDWIDTH PRODUCT

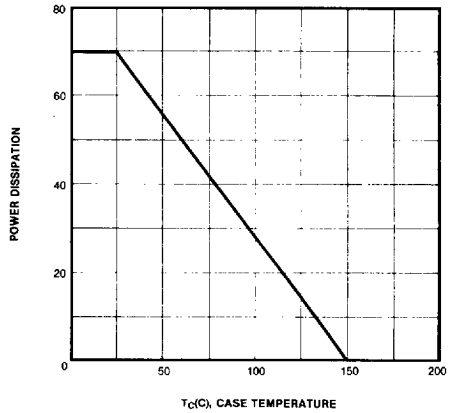


ELECTRONICS

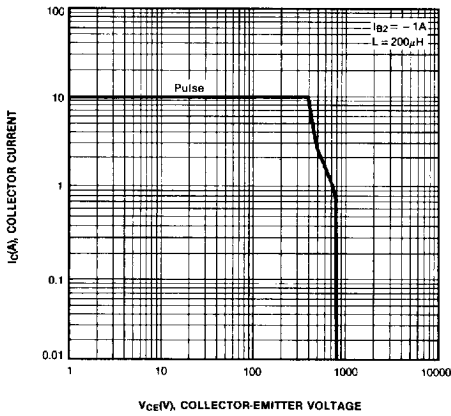
SWITCHING TIME



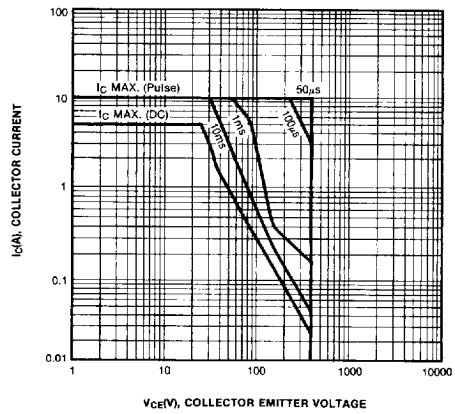
POWER DERATING



REVERSE BIAS SAFE OPERATING AREA



SAFE OPERATING AREA



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